

WHAT IS CLAIMED IS:

1. A nonvolatile memory apparatus comprising:
 - a control circuit;
 - a plurality of terminals including a clock terminal, a command terminal and other terminal;
 - a data buffer;
 - a command buffer; and
 - a plurality of nonvolatile memory cells,wherein said clock terminal receives a clock signal,
wherein said command terminal couples to said command buffer and receives commands which comprise a read command and a program command,
wherein said data buffer is used for receiving data from outside and outputting data to outside,
wherein said control circuit reads out operation steps from a program memory for controlling an operation of said received command by executing said operation steps.
wherein in an operation in response to said read command, said control circuit controls, based on operation steps corresponding to said read command, reading data from ones of said nonvolatile memory cells, stores read data to said data buffer, and outputting said read data stored in said data buffer via said other terminal except said command terminal in response to said clock signal, and
wherein in an operation in response to said program command received from said command terminal, said control circuit controls, based on

operation steps corresponding to said program command, receiving data via said other terminal except said command terminal in response to clock signal, stores received data to said data buffer and writing said received data to ones of said nonvolatile memory cells.

2. A nonvolatile memory apparatus according to claim 1, further comprising;

a decode circuit,

wherein said decode circuit decodes said commands received in said command buffer.

3. A nonvolatile memory apparatus according to claim 2, wherein each of said nonvolatile memory cells has a threshold voltage within an arbitrary one of a plurality of threshold voltage ranges,

wherein said threshold voltage ranges comprise a threshold voltage range indicating an erase state and a threshold voltage range indicating a program state, and

wherein said nonvolatile memory apparatus controls moving said threshold voltage of one nonvolatile memory cell to within said threshold voltage range indicating said program state and staying threshold voltages of remaining memory cells of ones of said nonvolatile memory cells within said threshold voltage range indicating said erase state, based on said operation steps corresponding to said program command.

4. A nonvolatile memory apparatus according to claim 3, wherein

said command further comprises:

an erase command,

wherein in an operation in response to said erase command received from said command terminal, said control circuit controls, based on operation steps corresponding to said erase command, erasing of data stored in ones of said nonvolatile memory cells, and

wherein said control circuit controls moving said threshold voltages of ones of said nonvolatile memory cells to within said threshold voltage range indicating said erase state, based on said operation steps corresponding to said erase command.

5. A nonvolatile memory apparatus according to claim 4, wherein said control circuit comprises a circuit, and

wherein in said operation in response to read command, said circuit senses status of data according to threshold voltage of said nonvolatile memory cell which is within whether said threshold voltage range indicating said erase state or said threshold voltage range indicating said program state.

6. A nonvolatile memory apparatus according to claim 5, wherein said other terminal is a data terminal,

wherein in said operation in response to said program command, said data terminal receives data in response to said clock signal, and

wherein in said operation in response to said read command, said data terminal outputs data in response to said clock signal.

7. A nonvolatile memory apparatus according to claim 1, wherein said control circuit includes said program memory therein.

8. A nonvolatile memory apparatus according to claim 2, wherein each of said nonvolatile memory cells has a threshold voltage within an arbitrary one of a plurality of threshold voltage ranges,

wherein said threshold voltage ranges comprise a threshold voltage range indicating an erase state and a plurality of threshold voltage ranges each indicating a corresponding program state, and

wherein said nonvolatile memory apparatus controls moving said threshold voltage of one nonvolatile memory cell to within one of said threshold voltages indicating said program states according to data and staying said threshold voltages of remaining memory cells of ones of said nonvolatile memory cells, based on said operation steps corresponding to said program command.

9. A nonvolatile memory apparatus according to claim 8, wherein said command further comprises:

an erase command,

wherein in an operation in response to said erase command received from said command terminal, said control circuit controls, based on operation steps corresponding to said erase command, erasing of data stored in ones of said nonvolatile memory cells, and

wherein said control circuit controls moving said threshold voltages of ones of nonvolatile memory cells to within said threshold voltage range

indicating said erase state, based on said operation steps corresponding to said erase command.

10. A nonvolatile memory apparatus comprising:
 - a control circuit;
 - a first volatile memory;
 - a second volatile memory;
 - a clock terminal;
 - a data terminal;
 - a command terminal; and
 - a plurality of nonvolatile memory cells,wherein said clock terminal receives a clock signal,
wherein said data terminal couples to said first volatile memory,
wherein said command terminal couples to said second volatile memory receives commands which include a read command and a program command,
wherein said control circuit executes operation steps corresponding to a received command read out from a program memory,
wherein in an operation in response to said read command received from said command terminal, said control circuit controls, based on operation steps corresponding to said read command, reading data from ones of said nonvolatile memory cells, transferring read data to said first volatile memory, and serially outputting said read data from said first volatile memory via said data terminal in response to said clock signal, and
wherein in an operation in response to said program command

received from said command terminal, said control circuit controls, based on operation steps, corresponding to said program command, serially receiving of data via said data terminal in response to said clock signal, transferring received data to said first volatile memory, and writing said received data stored in said first volatile memory to ones of said nonvolatile memory cells.

11. A nonvolatile memory apparatus according to claim 10, further comprising:

a decode circuit,

wherein said decode circuit decodes said commands received in said second volatile memory.

12. A nonvolatile memory apparatus according to claim 11, wherein each of said nonvolatile memory cells has a threshold voltage within an arbitrary one of a plurality of threshold voltage ranges,

wherein said threshold voltage ranges comprise a threshold voltage range indicating an erase state and a threshold voltage range indicating a program state, and

wherein said nonvolatile memory apparatus controls moving said threshold voltage of one nonvolatile memory cell to within said threshold voltage range indicating said program state and staying threshold voltages of remaining memory cells of ones of said nonvolatile memory cells within said threshold voltage range indicating said erase state, based on said operation steps corresponding to said program command.

13. A nonvolatile memory apparatus according to claim 12, wherein said command further comprises:

an erase command,

wherein in an operation in response to said erase command received from said command terminal, said control circuit controls, based on operation steps corresponding to said erase command, erasing of data stored in ones of said nonvolatile memory cells, and

wherein said control circuit controls moving said threshold voltage of ones of nonvolatile memory cells to within said threshold voltage range indicating said erase state, based on said operation steps corresponding to said erase command.

14. A nonvolatile memory apparatus according to claim 13, wherein said control circuit comprises a circuit, and

wherein in said operation in response to read command, said circuit senses status of data according to threshold voltage of said nonvolatile memory cell which is within whether said threshold voltage range indicating said erase state or said threshold voltage range indicating said program state.

15. A nonvolatile memory apparatus according to claim 10, wherein said control circuit includes said program memory therein.

16. A nonvolatile memory apparatus according to claim 11, wherein each of said nonvolatile memory cells has a threshold voltage within an arbitrary one of a plurality of threshold voltage ranges,

wherein said threshold voltage ranges comprise a threshold voltage range indicating an erase state and a plurality of threshold voltage ranges each of indicating a corresponding program state, and

wherein said nonvolatile memory apparatus controls moving said threshold voltage of one nonvolatile memory cell to within one of said threshold voltage ranges indicating said program states according to data and staying said threshold voltages of remaining memory cells of ones of said nonvolatile memory cells, based on said operation steps corresponding to said program command.

17. A nonvolatile memory apparatus according to claim 16, wherein said command further comprises:

an erase command,

wherein in an operation in response to said erase command received from said command terminal, said control circuit controls, based on operation steps corresponding to said erase command, erasing of data stored in ones of said nonvolatile memory cells, and

wherein said control circuit controls moving said threshold voltages of ones of nonvolatile memory cells to within said threshold voltage range indicating said erase state, based on said operation steps corresponding to said erase command.